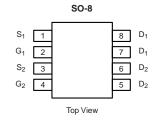
Dual P-Channel 25 V (D-S) MOSFET

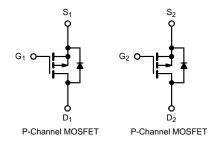
PRODUCT SUMMARY				
V _{DS} (V)	- 25			
$R_{DS(on)}(\Omega)$ at V_{GS} = - 10 V	0.051			
$R_{DS(on)} (\Omega)$ at $V_{GS} = -4.5 V$	0.063			
I _D (A) per leg	-5.4			
Configuration	Dual			

FEATURES

- DT-Trench Power MOSFET
- AEC-Q101 Qualified^c
- 100 % R_g and UIS Tested







ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	- 25	V	
Gate-Source Voltage		V _{GS}	± 12	v	
Continuous Drain Current	T _C = 25 °C	1	- 5.4		
	T _C = 125 °C	I _D	- 3.8		
Continuous Source Current (Diode Conduction)		I _S	- 3	А	
ulsed Drain Current ^a		I _{DM}	- 26		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	- 17		
Single Pulse Avalanche Energy	L = 0.1 MH	E _{AS}	14	mJ	
Maximum Power Dissipation ^a	T _C = 25 °C	P	3.3	W	
	T _C = 125 °C	P _D	1.1	vv	
Operating Junction and Storage Temperature	e Range	T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER	SYMBOL	LIMIT	UNIT			
Junction-to-Ambient PCB M	ount ^b R _{thJA}	110	°C/W			
Junction-to-Foot (Drain)	R _{thJF}	45	C/W			

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$

b. When mounted on 1" square PCB (FR-4 material).

c. Parametric verification ongoing.

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SPECIFICATIONS ($T_c = 25 \text{ °C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT
Static	•				•		•
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_D = -250 \mu A$		- 25	-	-	v
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = -250 \ \mu A$		- 1.0	- 1.5	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = -25 V	-	-	- 1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = -25 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	- 50	μA
		$V_{GS} = 0 V$	$V_{DS} = -25 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	- 150	1
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 10 V	$V_{DS} \le -5 V$	- 20	-	-	Α
		V _{GS} = - 10 V	I _D = - 3.9 A	-	0.051	0.063	
Drain-Source On-State Resistance ^a	Б	V _{GS} = - 10 V	I _D = - 3.9 A, T _J = 125 °C	-	0.061	0.072	Ω
Drain-Source On-State Resistance	R _{DS(on)}	$V_{GS} = -10 V$	I _D = - 3.9 A, T _J = 175 °C	-	0.082	0.086	
		V _{GS} = - 4.5 V	I _D = - 2.7 A	-	0.063	0.078	
Forward Transconductanceb	9 _{fs}	V _{DS} =	- 15 V, I _D = - 4.9 A	-	9	-	S
Dynamic ^b	•				•		
Input Capacitance	C _{iss}	V _{GS} = 0 V V _{DS} = - 25 V, f = 1 MHz		-	557	670	
Output Capacitance	C _{oss}		-	126	190	pF	
Reverse Transfer Capacitance	C _{rss}			-	90	115	1
Total Gate Charge ^c	Qg			-	15	22	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = - 10 V	$V_{DS} = -15 \text{ V}, \text{ I}_{D} = -4.9 \text{ A}$	-	2.1		nC
Gate-Drain Charge ^c	Q _{gd}			-	3.5	-	1
Gate Resistance	Rg		f = 1 MHz		5.26	8.50	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	3	5	
Rise Time ^c	tr	V_{DD} = - 15 V, R _L = 6.8 Ω I _D ≅ - 1 A, V _{GEN} = - 10 V, R _g = 1 Ω		-	9	14	- ns
Turn-Off Delay Time ^c	t _{d(off)}			-	20	30	
Fall Time ^c	t _f			-	9	14	
Source-Drain Diode Ratings and Char	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	- 26	Α
Forward Voltage	V _{SD}	I _F = - 2 A, V _{GS} = 0 V		-	- 0.8	- 1.2	V

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~$ %.

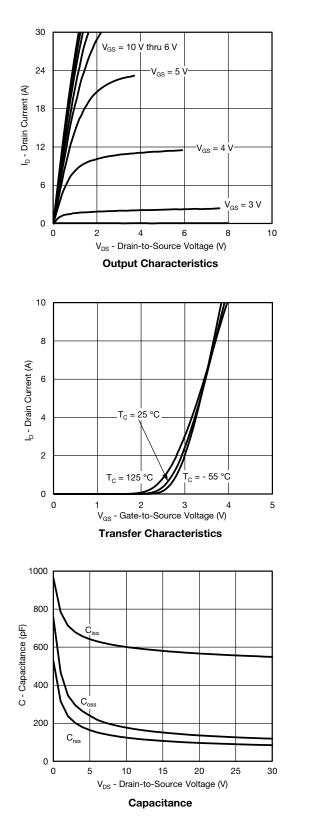
b. Guaranteed by design, not subject to production testing.

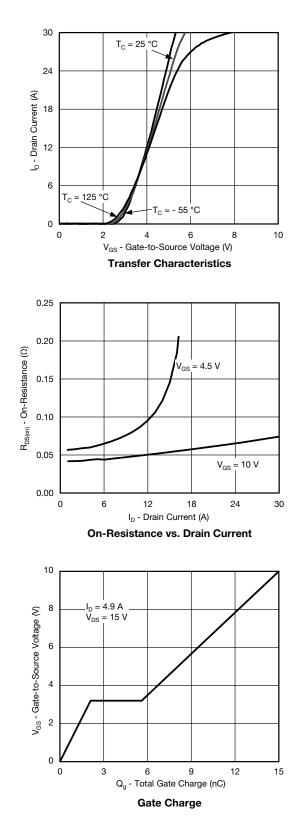
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



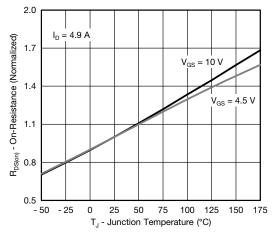
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



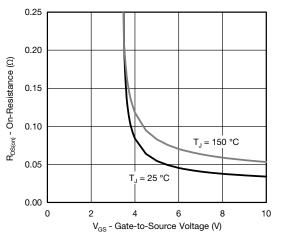


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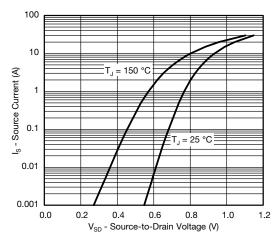
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



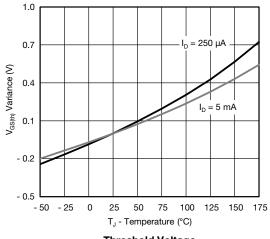
On-Resistance vs. Junction Temperature



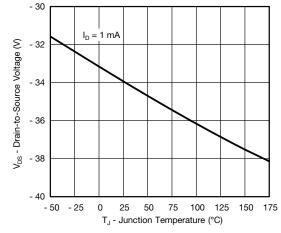
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage

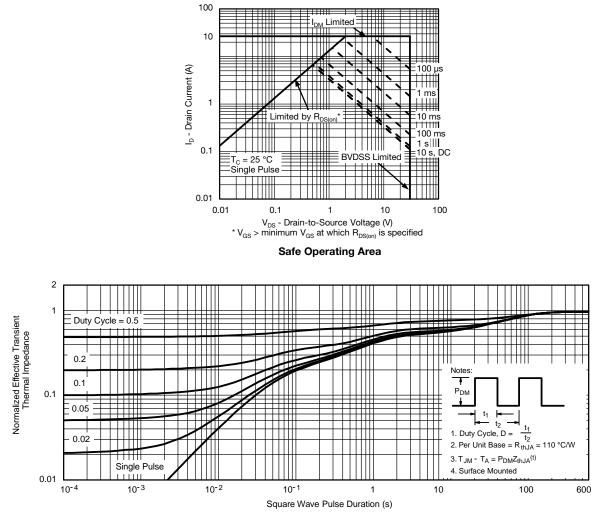






Drain Source Breakdown vs. Junction Temperature

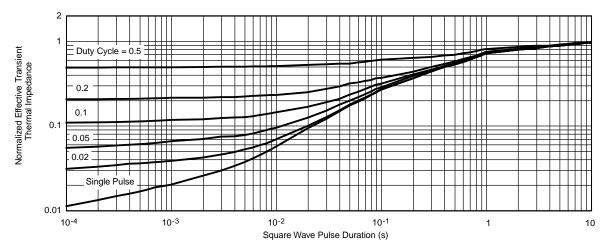
THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

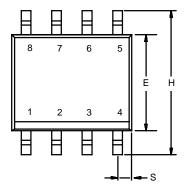
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

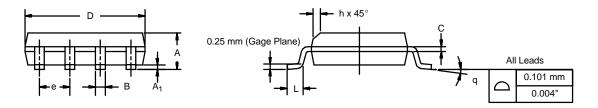


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SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012





	MILLIM	IETERS	INC	HES	
DIM	Min	Мах	Min	Max	
A	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.27 BSC		0.050 BSC		
н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498					



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)



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